

< C band internally matched power GaAs FET >

MGFC40V5964

5.9 - 6.4 GHz BAND / 10W

DESCRIPTION

The MGFC40V5964 is an internally impedance-matched GaAs power FET especially designed for use in 5.9 - 6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

• High output power

P1dB=10W (TYP.) @f=5.9 - 6.4GHz

• High power gain

GLP=10dB (TYP.) @f=5.9 - 6.4GHz

High power added efficiency

P.A.E.=30% (TYP.) @f=5.9 - 6.4GHz

• Low distortion [item -51]

IM3=-49dBc (TYP.) @Po=29dBm S.C.L

APPLICATION

• item 01: 5.9 - 6.4 GHz band power amplifier

• item 51: 5.9 - 6.4 GHz band digital radio communication

QUALITY

• IG

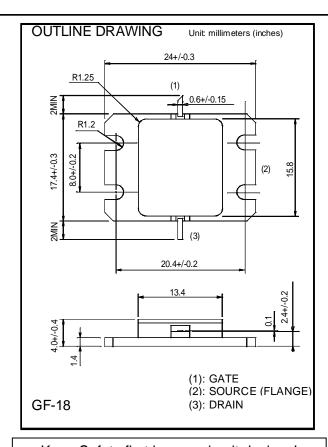
RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A • RG=50ohm Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Unit
V
V
Α
mΑ
mΑ
W
°C
°C

1 : Tc=25°C



Keep Safety first in your circuit designs! Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (I) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	4.5	6	Α
gm	Transconductance	VDS=3V,ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=40mA	-2	-3	-4	٧
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	39.5	40.5	-	dBm
GLP	Linear Power Gain	f=5.9 – 6.4GHz	8	10	-	dB
ID	Drain current		-	2.4	-	Α
P.A.E.	Power added efficiency		-	30	-	%
IM3 *2	3rd order IM distortion		-42	-49	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	3	3.5	°C/W

^{*2 :}item -51 ,2 tone test,Po=29dBm Single Carrier Level ,f=6.4GHz,delta f=10MHz

^{*3:} Channel-case

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